

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
-20V	80m $\Omega$ @ $V_{GS} = 4.5\text{V}$	-2.7A
	110m $\Omega$ @ $V_{GS} = 2.5\text{V}$	-2.1A

## Description

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.


## Applications

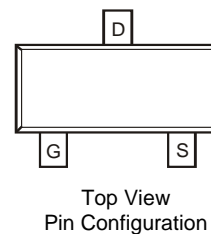
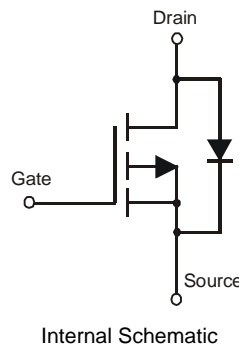
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor control

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

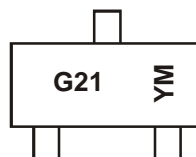


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2301U-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

## Marking Information



G21 = Product Type Marking Code  
YM = Date Code Marking  
Y = Year (ex: W = 2009)  
M = Month (ex: 9 = September)

### Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018		
Code	W	X	Y	Z	A	B	C	D	E	F		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-2.7	A
		T <sub>A</sub> = +70°C		-2.1	
Continuous Drain Current (Note 5) V <sub>GS</sub> = -2.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-2.1	A
		T <sub>A</sub> = +70°C		-1.7	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-27	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.8	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	157	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.45	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	80	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.8A
				110		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	10	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.8A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.75	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	608	—	pF	V <sub>DS</sub> = -6V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	82	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	72	—	pF	
Gate Resistance	R <sub>G</sub>	—	44.9	—	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	6.5	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -3A
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.5	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	12.5	40	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 10Ω, R <sub>G</sub> = 1.0Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>r</sub>	—	10.3	30	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	46.5	140	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	22.2	66	ns	

- Notes:
3. Device mounted on FR-4 PCB with minimum recommended pad layout.
  4. Repetitive rating, pulse width limited by junction temperature..
  5. Short duration pulse test used to minimize self-heating effect.
  6. Guaranteed by design. Not subject to production testing.